

Peter Rudolph

“Crystal defects”



Peter Rudolph is currently acting as consultant for research and industry at Crystal Technology Consulting (CTC) bureau. He was retired 2010 and finished 2011 his employment as head of the technology department at the Leibniz-Institute for Crystal Growth in Berlin. Here he dealt with the growth of semiconductor crystals (GaAs, InP, Ge, Si) by melt crystallization methods, especially LEC and VGF in non-steady magnetic fields. He was responsible for developments on photovoltaic silicon growth in cooperation with industrial partners. He obtained the diploma and PhD on electronic technology at the Dept. of Solid State Physics at the Technical University of Lviv (Ukraine) in 1972, and in 1985 the Professor position at the Humboldt University in Berlin. From 1993-94 and 1999 he was Guest Professor at the Tohoku University in Sendai (Japan). Until that time he dealt with growth of PbTe, CdTe, (Hg,Cd)Te, ZnSe and oxides. He is associate editor of J. Crystal Growth, vice president of the German Society of Crystal Growth and member of the IOCG executive committee. His academic literature comprises 1 monography, 36 monograph contributions and editions, 160 original papers and 35 patents. He taught fundamentals of phase transition, crystal growth kinetics and technologies, and defect formation in more than 15 countries. He received innovation prizes in 2001 and 2008.